

ABSTRACT

A semiconductor device of the present invention includes a MISFET provided in an element formation region Re of a semiconductor substrate **11** and a trench isolation **13** surrounding the sides of the element formation region Re. An oxygen-passage-suppression film **23** is provided from the top of the trench isolation **13** to the top of a portion of the element formation region Re adjacent to the trench isolation **13**. The oxygen-passage-suppression film **23** is made of a silicon nitride film or the like through which oxygen is less likely to permeate. Therefore, since it becomes hard that the upper edge of the element formation region Re of the semiconductor substrate **11** is oxidized, an expansion of the volume of the upper edge is suppressed, thereby reducing a stress.